

# Femtosecond laser interference patterning for highly accurate material structuring

Irene Solana<sup>1,\*</sup>, Fernando Chacon-Sanchez<sup>1</sup>, Mario Garcia-Lechuga<sup>1</sup>, and Jan Siegel<sup>1,\*</sup>

<sup>1</sup> Laser Processing Group, Instituto de Óptica Daza de Valdés (IO), CSIC, Serrano 121, 28006 Madrid, Spain

\*Corresponding author email: [isolana@io.cfmac.csic.es](mailto:isolana@io.cfmac.csic.es)

The use of fast and ultrafast laser pulses is nowadays a well-established technique for micro- and nano-structuring of materials. Direct laser interference patterning (DLIP) with ps and ns pulses has evolved into a promising technique for material micro-structuring thanks to the precise and controlled energy deposition achieved through the interference of two or more coherent laser beams, which allows to fabricate a wide variety of structures in a broad range of materials [1].

When using ultrashort laser pulses, one of the major issues of this technique is the need of a nearly perfect temporal and spatial overlap between the interfering beams. To achieve this, we made use of an imaging set-up by combining commercial or ad-hoc laser-fabricated diffractive optical elements (DOE) with a demagnifying optical system. High-contrast, well-defined excitation profiles with a Gaussian envelope and periods between 5  $\mu\text{m}$  and 650 nm (Fig. 1a) can be achieved employing a commercial Ti:Sa amplified laser (800 nm, 120 fs, 1 mJ) by slightly changing the irradiation configuration. We employed this setup to obtain amorphous or ablative nanostructures in crystalline silicon (Fig 1b-c). The topography of the amorphized regions of the sample shows a strong dependence on the imprinted fringe width (Fig 1d-e). Moreover, we demonstrate the versatility and scalability of this technique by imprinting micro-dots of 1  $\mu\text{m}$ -600 nm diameter (Fig. 1f) and large area (5 mm x 5 mm) nanogratings (Fig 1g).

The results obtained allow a detailed investigation of the mechanisms responsible for the surface deformation, including melting, Marangoni convection, capillary waves, and resolidification [2]. Furthermore, the technique's exceptional upscaling capacity renders it highly appropriate for industrial applications.

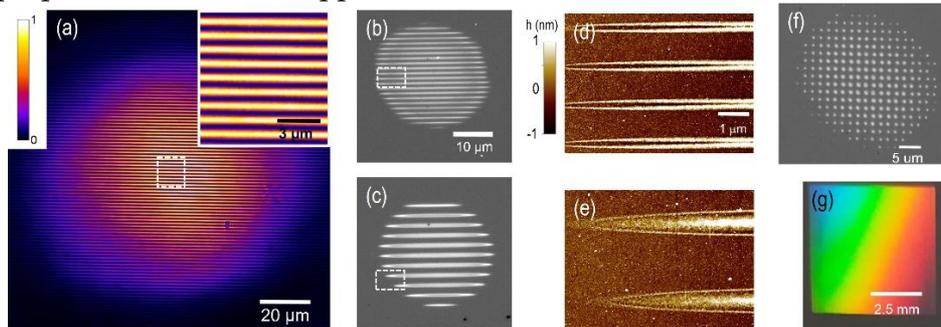


Fig 1. (a) 1.25  $\mu\text{m}$  periodic laser intensity distribution at the sample plane. Inset shows the zoomed image of the selected area. (b-c) Optical microscopy images of single shot imprinted patterns in c-Si with 1.25  $\mu\text{m}$  (b) and 2.52  $\mu\text{m}$  periodicity. (d-e) AFM map of the outlined areas in (b-c). (f) Optical microscopy image of a dot-like pattern. (g) Macroscopic image of a large-area grating with 1.25  $\mu\text{m}$  period, illuminated by white light.

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